

IN THE SPECIFICATION

Please rewrite the paragraphs on page 8, lines 1-11 as follows:

B1 The operation of the first mode of the invention is explained, referring to the timing chart as shown in Figure 1, concerning about the interlace solid-state image pickup device with the vertical OFD for the blooming control. The structure of the interlace solid-state image pickup device is explained, referring to Figures 7 to 9 and 12, 9.

Firstly, in order to reset the charges in photo-electric conversion unit 101 ~~are reset~~ at t_1 , a reverse bias voltage $V_{H\text{sub}}$ is applied to N semiconductor substrate 107 as shown in Figures 2, 8 and 9. Hereupon, the charges in photo-electric conversion unit 101 are swept out into N semiconductor substrate 107, because N semiconductor region 109 and P semiconductor region 108 become complete depletion layers.

Please rewrite the paragraph on page 9, lines 3-7, as follows:

B2 The electric potential ϕ' is preferably deeper than ϕ tg which is given by the voltage $V_{M\text{cl}}$ which is applied, during the times except the read-out step, to second charge transfer electrode 106 in signal read-out portion 120 adjacent to photo-electric conversion unit 101 as shown in Figure 12. 101.